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Patent Number: JP2001172767
Publication date: 2001-06-26
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Requested Patent: ☐ JP2001172767
Application Number: JP20000315409 20001016
Priority Number(s):
IPC Classification: C23C16/40; C23C16/02; C23C16/18; H01L21/316
EC Classification:
EC Classification:
Equivalents: FI992223

Abstract

PROBLEM TO BE SOLVED: To provide a method of growing an oxide thin film on a substrate.
SOLUTION: In the method of growing an oxide thin film according to the principle of the ALD method where an oxide thin film is deposited onto a substrate by an alternating surface reaction of metallic raw material and oxygen raw material, the oxygen raw material to be used is composed of a compound of boron, silicon or metal having at least one organic ligand, and the oxygen is combined with at least one atom of boron, silicon or metal.